



NCE N-Channel Enhancement Mode Power MOSFET

Description

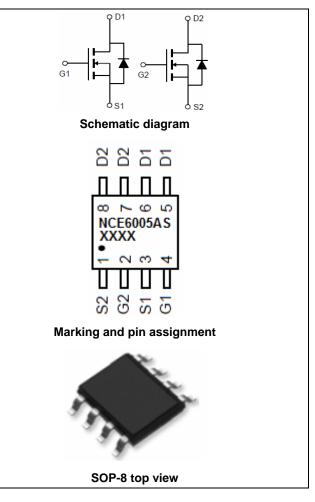
The NCE6005AS uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS}=60V,I_D=5A
 R_{DS(ON)} <35mΩ @ V_{GS}=10V (Typ.26mΩ)
 R_{DS(ON)} <45mΩ @ V_{GS}=4.5V (Typ.32mΩ)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity	
NCE6005AS	NCE6005AS	SOP-8	Ø330mm	12mm	2500 units	

Absolute Maximum Ratings (T_A=25[°]Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	5	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	3.5	А
Pulsed Drain Current	I _{DM}	24	А
Maximum Power Dissipation	PD	2	W
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{θJA}	62.5	°C/W	
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Electrical Characteristics (T_A=25 $^{\circ}$ Cunless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)			1			L
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	1.2	1.6	2.5	V
	R _{DS(ON)}	V _{GS} =10V, I _D =5A	-	26	35	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =5A	-	32	45	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =5A	11	-	-	S
Dynamic Characteristics (Note4)			1			
Input Capacitance	Clss		-	979	-	PF
Output Capacitance	Coss	V _{DS} =30V,V _{GS} =0V,	-	120	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	100	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t _{d(on)}		-	5.2	-	nS
Turn-on Rise Time	tr	V_{DD} =30V, R _L =6.7 Ω	-	3	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =3 Ω	-	17	-	nS
Turn-Off Fall Time	t _f		-	2.5	-	nS
Total Gate Charge	Qg)/ 00)// EA	-	22		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V,I_{D}=5A,$	-	3.3		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	-	5.2		nC
Drain-Source Diode Characteristics						1
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =5A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	5	А
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD				

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition:Tj=25 $^\circ\!\mathrm{C}$,VDD=30V,VG=10V,L=0.5mH,Rg=25 Ω

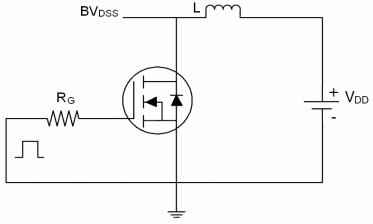


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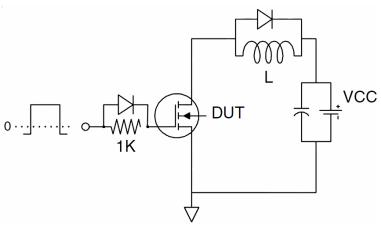
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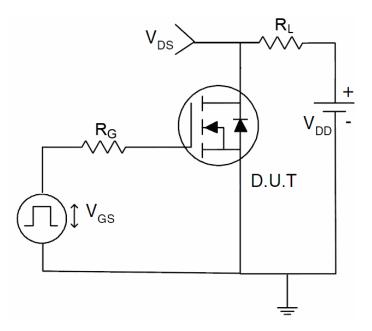
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



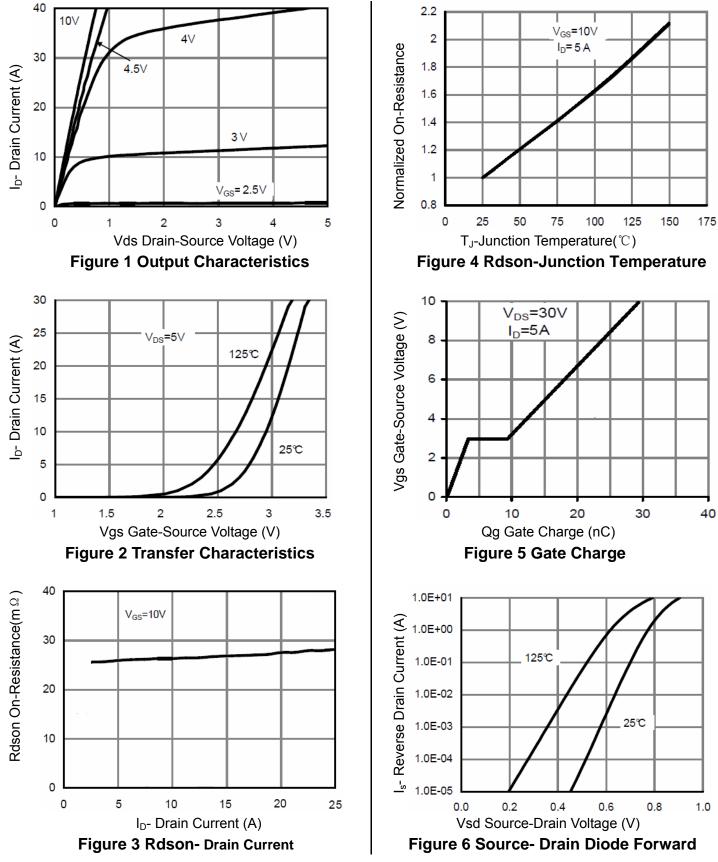
3) Switch Time Test Circuit









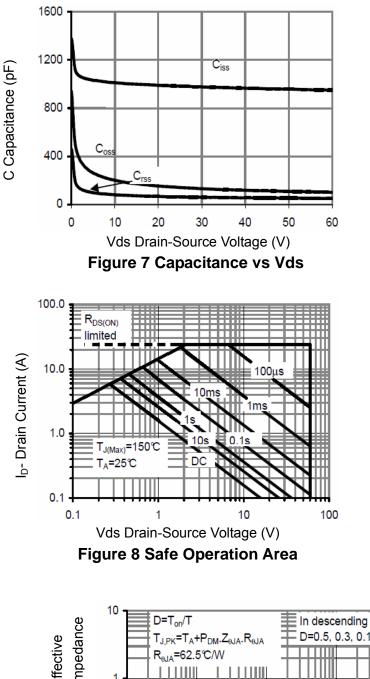




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NCE6005AS



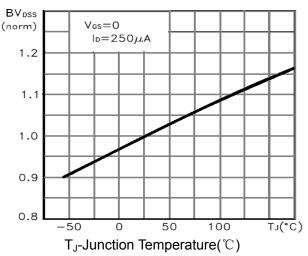


Figure 9 BV_{DSS} vs Junction Temperature

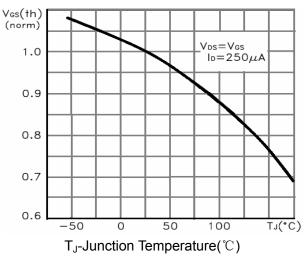
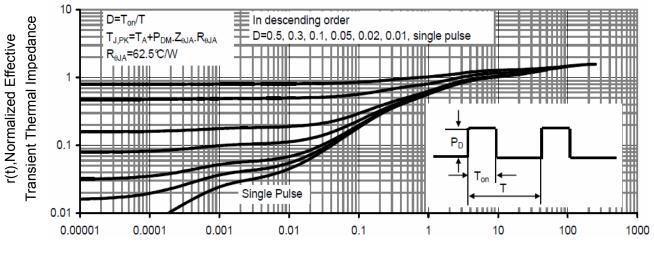
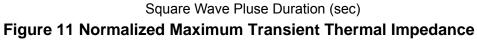


Figure 10 V_{GS(th)} vs Junction Temperature



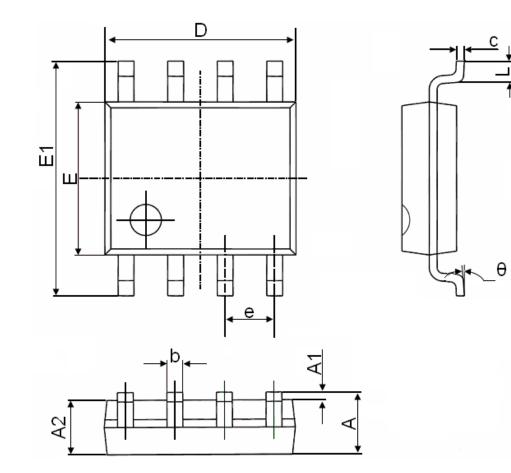




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SOP-8 Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.006	0.010	
D	4.700	5.100	0.185	0.200	
E	3.800	4.000	0.150	0.157	
E1	5.800	6.200	0.228	0.244	
е	1.270	(BSC)	0.050	(BSC)	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	







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